

TRAN(NPN)SISTOR (NPN)

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Features

- Small package.
- -Complementary to MMBT3906M

Package and Pin Configuration



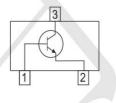
Circuit diagram

Mechanical data

- Case: SOT-723, molded plastic.

- Terminals: Solderable per MIL-STD-750,

method 2026.

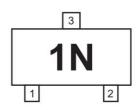


- 1.BASE - 2.EMITTER - 3.COLLECTOR



SOT723

Marking



Maximum Ratings (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Value	Unit
Collector-Base voltage		Vсво	60	V
Collector-Emitter voltage		VCEO	40	V
Emitter-Base voltage		Vebo	6	V
Collector current-continuous		lc	0.2	A
Power dissipation		Pc	0.1	W
Thermal resistance	junction to ambient	Reja	1250	°C/W
Junction temperature		TJ	150	°C
Storage temperature range		Tstg	-55~+150	°C



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Parameter	Symbol	Conditions	Min	Max	Unit
Collector-Base breakdown voltage	V(BR)CBO	Ic=10μΑ, Iε=0	60		V
Collector-Emitter breakdown voltage	V(BR)CEO	Ic=1mA, IB=0	40		V
Emitter-Base breakdown voltage	V(BR)EBO	Iε=10μΑ, Ic=0	6		V
Collector cut-off current	ICEX	VCE=30V, VEB(off)=3V		50	nA
Emitter cut-off current	I EBO	V _{EB} =5V, Ic=0		100	nA
DC current gain	hfe(1)	Vce=1V, Ic=0.1mA	40		
	hfe(2)	Vce=1V, lc=1mA	70		1
	hfe(3)	Vce=1V, Ic=10mA	100	300	1
	hfe(4)	Vce=1V, Ic=50mA	60		1
Collector-Emitter saturation voltage	VCE(sat)1	Ic=10mA, Iв=1mA		0.2	V
	VCE(sat)2	Ic=50mA, Iв=5mA		0.3	V
Base-Emitter saturation voltage	VBE(sat)1	Ic=10mA, Iв=1mA	0.65	0.85	V
	VBE(sat)2	lc=50mA, Iв=5mA		0.95	V
Transition frequency	fτ	Vce=20V, Ic=10mA, f=100MHz	300		MHz
Output capacitance	Соь	Vcb=5V, IE=0, f=1MHz		4	pF
Input capacitance	Cib	VEB=0.5V, Ic=0, f=1MHz		8	pF
Noise figure	NF	Vce=5V, Ic=0.1mA, f=1MHz, Rs=1KΩ		5	dB
Delay time	ta	Vcc=3V, Vbe(off)=-0.5V		35	nS
Rise time	tr	Ic=10mA, I _{B1} =1mA		35	nS
Storage time	ts	Vcc=3V. lc=10mA		200	nS
Fall time	tr	I _{B1} =I _{B2} =1mA		50	nS

Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

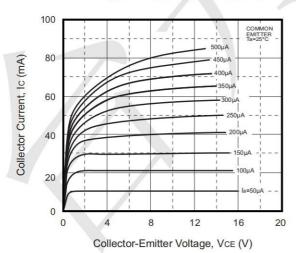


Fig.1 - Static Characteristic

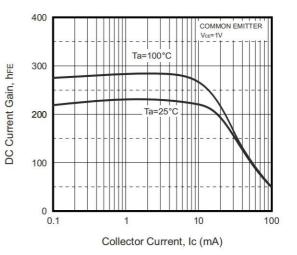
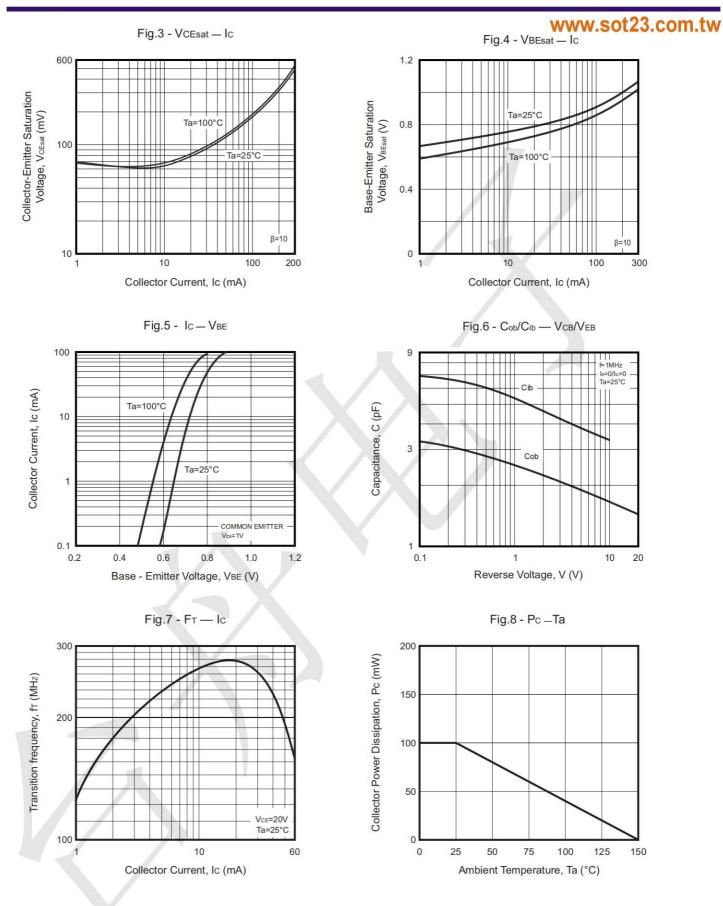


Fig.2 - hfe - Ic



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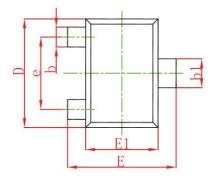


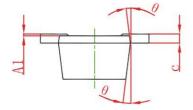


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SOT-723 Package Outline Dimensions





A	

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
А	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
С	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
е	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	

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